Antonio Polimeni

List of Publications by Year in Descending Order

231 papers	4,072 citations	36 h-index	50 g-index
249 ext. papers	4,481 ext. citations	4.5 avg, IF	4.89 L-index

#	Paper	IF	Citations
231	Vibrational Properties in Highly Strained Hexagonal Boron Nitride Bubbles.. *Nano Letters*, **2022**,	11.5	2
230	Selective Effects of the Host Matrix in Hydrogenated InGaAsN Alloys: Toward an Integrated Matrix/Defect Engineering Paradigm. *Advanced Functional Materials*, **2022**, 32, 2108862	15.6	
229	Tailoring the optical properties of 2D transition metal dichalcogenides by strain. *Optical Materials*, **2022**, 125, 112087	3.3	0
228	Photoluminescence Spectroscopy Applied to Semiconducting Nanowires: A Valuable Probe for Assessing Lattice Defects, Crystal Structures, and Carriers Temperature **2021**, 289-306		
227	Towards free-standing graphane: atomic hydrogen and deuterium bonding to nano-porous graphene. *Nanotechnology*, **2021**, 32, 035707	3.4	7
226	Brightly Luminescent and Moisture Tolerant Phenyl Viologen Lead Iodide Perovskites for Light Emission Applications. *Journal of Physical Chemistry Letters*, **2021**, 12, 5456-5462	6.4	2
225	Strain-tuning of the electronic, optical, and vibrational properties of two-dimensional crystals. *Applied Physics Reviews*, **2021**, 8, 021318	17.3	15
224	Transport mechanisms in Co-doped ZnO (ZCO) and H-irradiated ZCO polycrystalline thin films. *Physical Chemistry Chemical Physics*, **2021**, 23, 2368-2376	3.6	3
223	Tailoring the optical properties of dilute nitride semiconductors at the nanometer scale. *Nanotechnology*, **2021**, 32, 185301	3.4	
222	Experimental Adhesion Energy in van der Waals Crystals and Heterostructures from Atomically Thin Bubbles. *Physical Review Letters*, **2021**, 127, 046101	7.4	6
221	Exceptional Elasticity of Microscale Constrained MoS Domes. *ACS Applied Materials & Interfaces*, **2021**, 13, 48228-48238	9.5	4
220	Deuterium Adsorption on Free-Standing Graphene. *Nanomaterials*, **2021**, 11,	5.4	5
219	Imaging shape and strain in nanoscale engineered semiconductors for photonics by coherent x-ray diffraction. *Communications Materials*, **2020**, 1,	6	1
218	Broadband enhancement of light-matter interaction in photonic crystal cavities integrating site-controlled quantum dots. *Physical Review B*, **2020**, 101,	3.3	10
217	The Interaction of Hydrogen with the van der Waals Crystal -InSe. *Molecules*, **2020**, 25,	4.8	8
216	In-Situ Annealing and Hydrogen Irradiation of Defect-Enhanced Germanium Quantum Dot Light Sources on Silicon. *Crystals*, **2020**, 10, 351	2.3	5
215	Engineered Creation of Periodic Giant, Nonuniform Strains in MoS2 Monolayers. *Advanced Materials Interfaces*, **2020**, 7, 2000621	4.6	15

214	Evidence of the direct-to-indirect band gap transition in strained two-dimensional WS2, MoS2, and WSe2. *Physical Review Research*, **2020**, 2,	3.9	55
213	Nanoscale Measurements of Elastic Properties and Hydrostatic Pressure in H2-Bulged MoS2 Membranes. *Advanced Materials Interfaces*, **2020**, 7, 2001024	4.6	9
212	Hole and Electron Effective Masses in Single InP Nanowires with a Wurtzite-Zincblende Homojunction. *ACS Nano*, **2020**, 14, 11613-11622	16.7	6
211	Opposite Hydrogen Behaviors in GaAsN and InAsN Alloys: Band Gap Opening Versus Donor Doping. *Journal of Physical Chemistry C*, **2020**, 124, 19240-19251	3.8	3
210	N–H complexes in GaAs studied at the atomic scale by cross-sectional scanning tunneling microscopy. *Physical Review B*, **2020**, 102,	3.3	2
209	Giant magneto-optical response in H+ irradiated Zn1−xCoxO thin films. *Journal of Materials Chemistry C*, **2019**, 7, 78-85	7.1	9
208	Common nonlinear features and spin-orbit coupling effects in the Zeeman splitting of novel wurtzite materials. *Physical Review B*, **2019**, 99,	3.3	7
207	Unusual spin properties of InP wurtzite nanowires revealed by Zeeman splitting spectroscopy. *Physical Review B*, **2019**, 99,	3.3	9
206	Strain related relaxation of the GaAs-like Raman mode selection rules in hydrogenated GaAs1−xNx layers. *Journal of Applied Physics*, **2019**, 125, 175701	2.5	2
205	Plasmon-assisted bandgap engineering in dilute nitrides. *Nanophotonics*, **2019**, 8, 1465-1476	6.3	4
204	Coupled Photonic Crystal Nanocavities as a Tool to Tailor and Control Photon Emission. *Ceramics*, **2019**, 2, 34-55	1.7	1
203	Local magneto-optical response of H+ irradiated Zn1−xCoxO thin films. *European Physical Journal: Special Topics*, **2019**, 228, 683-687	2.3	4
202	Controlled Micro/Nanodome Formation in Proton-Irradiated Bulk Transition-Metal Dichalcogenides. *Advanced Materials*, **2019**, 31, e1903795	24	31
201	Spatially selective hydrogen irradiation of dilute nitride semiconductors: a brief review. *Semiconductor Science and Technology*, **2018**, 33, 053001	1.8	4
200	Site-Controlled Single-Photon Emitters Fabricated by Near-Field Illumination. *Advanced Materials*, **2018**, 30, e1705450	24	20
199	Azetidinium lead iodide: synthesis, structural and physico-chemical characterization. *Journal of Materials Chemistry A*, **2018**, 6, 10135-10148	13	9
198	Site-Controlled Quantum Emitters in Dilute Nitrides and their Integration in Photonic Crystal Cavities. *Photonics*, **2018**, 5, 10	2.2	9
197	Gallium clustering and structural effects of hydrogenation in InGaN/GaN nanostructures. *Journal of Applied Physics*, **2018**, 124, 165709	2.5	2

196	A lithographic approach for quantum dot-photonic crystal nanocavity coupling in dilute nitrides. *Microelectronic Engineering*, **2017**, 174, 16-19	2.5	9
195	Addressing the Fundamental Electronic Properties of Wurtzite GaAs Nanowires by High-Field Magneto-Photoluminescence Spectroscopy. *Nano Letters*, **2017**, 17, 6540-6547	11.5	9
194	Electronic properties of wurtzite-phase InP nanowires determined by optical and magneto-optical spectroscopy. *Applied Physics Reviews*, **2017**, 4, 041102	17.3	16
193	InP-InGaAs core-multi-shell nanowire quantum wells with tunable emission in the 1.3-1.55 μm wavelength range. *Nanoscale*, **2017**, 9, 13554-13562	7.7	8
192	Critical Temperature for the Conversion from Wurtzite to Zincblende of the Optical Emission of InAs Nanowires. *Journal of Physical Chemistry C*, **2017**, 121, 16650-16656	3.8	0
191	Bandgap Energy of Wurtzite InAs Nanowires. *Nano Letters*, **2016**, 16, 5197-203	11.5	37
190	Effect of the order-disorder transition on the optical properties of Cu2ZnSnS4. *Applied Physics Letters*, **2016**, 108, 211909	3.4	44
189	Long-Lived Hot Carriers in III-V Nanowires. *Nano Letters*, **2016**, 16, 3085-93	11.5	35
188	Ferromagnetism and Conductivity in Hydrogen Irradiated Co-Doped ZnO Thin Films. *ACS Applied Materials & Interfaces*, **2016**, 8, 12925-31	9.5	17
187	Value and Anisotropy of the Electron and Hole Mass in Pure Wurtzite InP Nanowires. *Nano Letters*, **2016**, 16, 6213-6221	11.5	14
186	Laser Level Scheme of Self-Interstitials in Epitaxial Ge Dots Encapsulated in Si. *Nano Letters*, **2016**, 16, 6802-6807	11.5	24
185	Temperature Dependence of Interband Transitions in Wurtzite InP Nanowires. *ACS Nano*, **2015**, 9, 4277-87	13.7	40
184	H-tailored surface conductivity in narrow band gap In(AsN). *Applied Physics Letters*, **2015**, 106, 022111	3.4	4
183	Synchrotron x-ray diffraction study of micro-patterns obtained by spatially selective hydrogenation of GaAsN. *Applied Physics Letters*, **2015**, 106, 051905	3.4	3
182	Genesis of Solitary Cations Induced by Atomic Hydrogen. *Advanced Functional Materials*, **2015**, 25, 5353-5359	11.8	5
181	Carrier masses and band-gap temperature sensitivity in Ga(AsBi) alloys. *Semiconductor Science and Technology*, **2015**, 30, 094002	1.8	10
180	Peculiarities of the hydrogenated In(AsN) alloy. *Semiconductor Science and Technology*, **2015**, 30, 105030	1.8	4
179	Polarized light absorption in wurtzite InP nanowire ensembles. *Nano Letters*, **2015**, 15, 998-1005	11.5	38

178	Single photons on demand from novel site-controlled GaAsN/GaAsN:H quantum dots. *Nano Letters*, **2014**, 14, 1275-80	11.5	28
177	Hydrogen effects in dilute III-N-V alloys: From defect engineering to nanostructuring. *Journal of Applied Physics*, **2014**, 115, 012011	2.5	9
176	Magneto-optical properties of wurtzite-phase InP nanowires. *Nano Letters*, **2014**, 14, 4250-6	11.5	21
175	Connections between local and macroscopic properties in solids: The case of N in III-V-N alloys. *Physical Review B*, **2014**, 89,	3.3	5
174	Nanoscale Tailoring of the Polarization Properties of Dilute-Nitride Semiconductors via H-Assisted Strain Engineering. *Physical Review Applied*, **2014**, 2,	4.3	9
173	H irradiation effects on the GaAs-like Raman modes in GaAs1-xNx/GaAs1-xNx:H planar heterostructures. *Journal of Applied Physics*, **2014**, 116, 245304	2.5	3
172	Effect of thermal annealing on defects in post-growth hydrogenated GaNP. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 561-563		1
171	Determination of exciton reduced mass and gyromagnetic factor of wurtzite (InGa)As nanowires by photoluminescence spectroscopy under high magnetic fields. *ACS Nano*, **2013**, 7, 10717-25	16.7	15
170	Effects of Bi incorporation on the electronic properties of GaAs: Carrier masses, hole mobility, and Bi-induced acceptor states. *Physica Status Solidi (B): Basic Research*, **2013**, 250, 779-786	1.3	15
169	Effects of hydrogen irradiation on the optical and electronic properties of site-controlled InGaAsN V-groove quantum wires **2013**,		1
168	Excitonic recombination and absorption in InxGa1−xAs/GaAs heterostructure nanowires. *Physical Review B*, **2013**, 87,	3.3	31
167	Nonresonant hydrogen dopants in In(AsN): A route to high electron concentrations and mobilities. *Physical Review B*, **2013**, 87,	3.3	8
166	Effects of hydrogen irradiation on the optical and electronic properties of site-controlled InGaAsN V-groove quantum wires. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 556-560		
165	A micrometer-size movable light emitting area in a resonant tunneling light emitting diode. *Applied Physics Letters*, **2013**, 103, 241105	3.4	2
164	Resonant depletion of photogenerated carriers in InGaAs/GaAs nanowire mats. *Applied Physics Letters*, **2013**, 102, 173102	3.4	11
163	Convergent beam electron-diffraction investigation of lattice mismatch and static disorder in GaAs/GaAs1−xNx intercalated GaAs/GaAs1−xNx:H heterostructures. *Applied Physics Letters*, **2012**, 101, 111912	3.4	1
162	Effects of hydrogenation on non-radiative defects in GaNP and GaNAs alloys: An optically detected magnetic resonance study. *Journal of Applied Physics*, **2012**, 111, 023501	2.5	4
161	Magneto-optical properties of single site-controlled InGaAsN quantum wires grown on prepatterned GaAs substrates. *Physical Review B*, **2012**, 85,	3.3	6

160	Photoluminescence: A Tool for Investigating Optical, Electronic, and Structural Properties of Semiconductors. *Springer Series in Materials Science*, **2012**, 125-170	0.9	1
159	Bi-induced p-type conductivity in nominally undoped Ga(AsBi). *Applied Physics Letters*, **2012**, 100, 092109	3.4	35
158	Hydrogen Incorporation in III-N-V Semiconductors: From Macroscopic to Nanometer Control of the Materials Physical Properties. *Advanced Functional Materials*, **2012**, 22, 1782-1801	15.6	24
157	Reduced temperature sensitivity of the polarization properties of hydrogenated InGaAsN V-groove quantum wires. *Applied Physics Letters*, **2012**, 101, 151114	3.4	5
156	Identification of four-hydrogen complexes in In-rich InxGa1 N (x>0.4) alloys using photoluminescence, x-ray absorption, and density functional theory. *Physical Review B*, **2012**, 86,	3.3	8
155	Effects of hydrogen on the electronic properties of Ga(AsBi) alloys. *Applied Physics Letters*, **2012**, 101, 222103	3.4	9
154	Band-gap profiling by laser writing of hydrogen-containing III-N-Vs. *Physical Review B*, **2012**, 86,	3.3	16
153	An all optical mapping of the strain field in GaAsN/GaAsN:H wires. *Applied Physics Letters*, **2012**, 101, 191908	3.4	5
152	Microscopic origin of compressive strain in hydrogen-irradiated dilute GaAs1 Ny alloys: Role of N-Hn centers with n>2 and their thermal stability. *Physical Review B*, **2012**, 86,	3.3	13
151	Giant and reversible enhancement of the electrical resistance of GaAs1 Nx by hydrogen irradiation. *Physical Review B*, **2011**, 84,	3.3	8
150	Laser writing of the electronic activity of N- and H-atoms in GaAs. *Applied Physics Letters*, **2011**, 99, 021105	3.4	7
149	Optical study of hydrogen-irradiated GaAsN/GaAs heterostructures. *Journal of Applied Physics*, **2011**, 109, 123511	2.5	9
148	Hydrogen-mediated nanostructuring of dilute nitride semiconductors. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 1195-1202	1.3	
147	Fabrication of site-controlled quantum dots by spatially selective incorporation of hydrogen in Ga(AsN)/GaAs heterostructures. *Advanced Materials*, **2011**, 23, 2706-10	24	38
146	Compositional evolution of Bi-induced acceptor states in GaAs1 Bix alloy. *Physical Review B*, **2011**, 83,	3.3	31
145	Room temperature spin filtering effect in GaNAs: Role of hydrogen. *Applied Physics Letters*, **2011**, 99, 152109	3.4	7
144	Deep levels in H-irradiated GaAs1-xNx (x . *Journal of Applied Physics*, **2011**, 110, 124508	2.5	8
143	Effect of postgrowth hydrogen treatment on defects in GaNP. *Applied Physics Letters*, **2011**, 98, 141920	3.4	7

142	Detailed structure of the H-N-H center in GaAsyN1−y revealed by vibrational spectroscopy under uniaxial stress. *Physical Review B*, **2010**, 81,	3.3	17
141	Quantum confinement effects in hydrogen-intercalated Ga1−xAsxNx-GaAs1−xNx:H planar heterostructures investigated by photoluminescence spectroscopy. *Physical Review B*, **2010**, 81,	3.3	6
140	Compositional dependence of the exciton reduced mass in GaAs1−xBix (x=0–10%). *Physical Review B*, **2010**, 81,	3.3	48
139	Hydrogen diffusion in GaAs1−xNx. *Physical Review B*, **2009**, 80,	3.3	23
138	Light polarization control in strain-engineered GaAsN/GaAsN:H heterostructures. *Applied Physics Letters*, **2009**, 94, 261905	3.4	16
137	Carrier mass measurements in degenerate indium nitride. *Physical Review B*, **2009**, 79,	3.3	23
136	Local structure of nitrogen-hydrogen complexes in dilute nitrides. *Physical Review B*, **2009**, 79,	3.3	18
135	Trends in the electronic structure of dilute nitride alloys. *Semiconductor Science and Technology*, **2009**, 24, 033001	1.8	84
134	Hydrogen-induced defect engineering in dilute nitride semiconductors. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, 2644-2648		2
133	Effective phonon bottleneck in the carrier thermalization of InAs/GaAs quantum dots. *Physical Review B*, **2008**, 78,	3.3	19
132	Effect of hydrogen incorporation temperature in in plane-engineered GaAsN□GaAsN:H heterostructures. *Applied Physics Letters*, **2008**, 92, 221901	3.4	12
131	In-plane band gap modulation investigated by secondary electron imaging of GaAsN/GaAsN:H heterostructures. *Applied Physics Letters*, **2008**, 93, 102116	3.4	9
130	Secondary Electrons Characterization of Hydrogenated Dilute Nitrides **2008**, 541-542		
129	Experimental evidence of different hydrogen donors in n-type InN. *Physical Review B*, **2008**, 77,	3.3	32
128	Influence of bismuth incorporation on the valence and conduction band edges of GaAs1−xBix. *Applied Physics Letters*, **2008**, 92, 262105	3.4	86
127	Role of strain and properties of N clusters at the onset of the alloy limit in GaAs1−xNx. *Physical Review B*, **2008**, 77,	3.3	15
126	Vibrational properties of the H-N-H complex in dilute III-N-V alloys: Infrared spectroscopy and density functional theory. *Physical Review B*, **2008**, 77,	3.3	19
125	Zero-phonon lines of nitrogen-cluster states in GaN As : H identified by time-resolved photoluminescence. *Journal of Materials Science*, **2008**, 43, 4344-4347	4.3	2

124	High-resolution X-ray diffractionin situstudy of very small complexes: the case of hydrogenated dilute nitrides. *Journal of Applied Crystallography*, **2008**, 41, 366-372	3.8	20
123	Photoluminescence under magnetic field and hydrostatic pressure for probing the electronic properties of GaAsN. *Physica Status Solidi (A) Applications and Materials Science*, **2008**, 205, 107-113	1.6	2
122	Controlled Band Gap Modulation of Hydrogenated Dilute Nitrides by SEM-Cathodoluminescence. *Springer Proceedings in Physics*, **2008**, 453-458	0.2	
121	Vibrational spectroscopy of hydrogenated GaP1−yNy. *Physica B: Condensed Matter*, **2007**, 401-402, 347-350	1.8	
120	Thermal evolution of small ND complexes in deuterated dilute nitrides revealed by in-situ high resolution X-ray diffraction. *Physica Status Solidi (A) Applications and Materials Science*, **2007**, 204, 2766-2771	1.6	0
119	Hydrostatic pressure experiments on dilute nitride alloys. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 24-31	1.3	3
118	X-ray absorption and diffraction study of II-VI dilute oxide semiconductor alloy epilayers. *Journal of Physics Condensed Matter*, **2007**, 19, 446201	1.8	2
117	Photoreflectance and reflectance investigation of deuterium-irradiated GaAsN. *Applied Physics Letters*, **2007**, 90, 091907	3.4	26
116	Electron mass in dilute nitrides and its anomalous dependence on hydrostatic pressure. *Physical Review Letters*, **2007**, 98, 146402	7.4	38
115	Formation and dissolution of D-N complexes in dilute nitrides. *Physical Review B*, **2007**, 76,	3.3	37
114	Hydrogen-induced Nitrogen Passivation in Dilute Nitrides: A Novel Approach to Defect Engineering. *Materials Research Society Symposia Proceedings*, **2007**, 994, 1		
113	Behavior of hydrogen in InN investigated in real time exploiting spectroscopic ellipsometry. *Applied Physics Letters*, **2007**, 91, 081917	3.4	8
112	Characteristics of InN grown on SiC under the In-rich regime by molecular beam heteroepitaxy. *Applied Physics Letters*, **2007**, 90, 011910	3.4	14
111	In-Plane Bandgap Engineering by Modulated Hydrogenation of Dilute Nitride Semiconductors. *Advanced Materials*, **2006**, 18, 1993-1997	24	48
110	Characterization of hydrogen passivated defects in strain-engineered semiconductor quantum dot structures. *Journal of Applied Physics*, **2006**, 100, 084313	2.5	8
109	Hydrogen-nitrogen complexes in dilute nitride alloys: Origin of the compressive lattice strain. *Applied Physics Letters*, **2006**, 89, 061904	3.4	34
108	Compositional disorder in GaAs1−xNx:H investigated by photoluminescence. *Physical Review B*, **2006**, 74,	3.3	11
107	Influence of nitrogen-cluster states on the gyromagnetic factor of electrons in GaAs1−xNx. *Physical Review B*, **2006**, 74,	3.3	43

106	Nitrogen-induced perturbation of the valence band states in GaP1−xNx alloys. *Physical Review B*, **2006**, 74,	3.3	12
105	Interaction between conduction band edge and nitrogen states probed by carrier effective-mass measurements in GaAs1−xNx. *Physical Review B*, **2006**, 73,	3.3	101
104	Passivation of an isoelectronic impurity by atomic hydrogen: The case of ZnTe:O. *Applied Physics Letters*, **2006**, 88, 101910	3.4	20
103	Correlation of band formation and local vibrational mode structure in Ga0.95Al0.05As1− Nx with 0 ≤x≤0.03. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 619-622		3
102	C2v nitrogen-hydrogen complexes in GaAsN revealed by X-ray Absorption Near-Edge Spectroscopy and ab initio simulations. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1836-1840		
101	Unusual effects of hydrogen on electronic and lattice properties of GaNP alloys. *Physica B: Condensed Matter*, **2006**, 376-377, 568-570	2.8	1
100	Competition of N-passivation and Te-passivation in hydrogenation of Te-doped (Ga,In)(N,As). *Physica E: Low-Dimensional Systems and Nanostructures*, **2006**, 32, 218-221	3	1
99	Carrier relaxation dynamics in annealed and hydrogenated (GaIn)(NAs)/GaAs quantum wells. *Applied Physics Letters*, **2005**, 87, 252111	3.4	8
98	Measurement of Carrier Localization Degree, Electron Effective Mass, and Excition Size in InxGa1−xAs1−yNy Alloys **2005**, 223-251		
97	Defect passivation in strain engineered InAs/(InGa)As quantum dots. *Materials Science and Engineering C*, **2005**, 25, 830-834	8.3	37
96	Free carrier and/or exciton trapping by nitrogen pairs in dilute GaP1−xNx. *Physical Review B*, **2005**, 71,	3.3	20
95	Effects of hydrogenation on the local structure of InxGa1−xAs1−yNy quantum wells and GaAs1−yNy epilayers. *Physical Review B*, **2005**, 72,	3.3	10
94	Nitrogen-hydrogen complex in GaAsxN1− revealed by x-ray absorption spectroscopy. *Physical Review B*, **2005**, 71,	3.3	55
93	Comparison between experimental and theoretical determination of the local structure of the GaAs1−yNy dilute nitride alloy. *Physical Review B*, **2005**, 71,	3.3	10
92	Magnetophotoluminescence studies of InxGa1−xAs1−yNy: a measurement of the electron effective mass, exciton size, and degree of carrier localization. *Journal of Physics Condensed Matter*, **2004**, 16, S3187-S3200	1.8	2
91	Vibrational spectroscopy of hydrogenated GaAs1−yNy: A structure-sensitive test of an H2*(N) model. *Physical Review B*, **2004**, 69,	3.3	40
90	Tunable variation of the electron effective mass and exciton radius in hydrogenated GaAs1−xNx. *Physical Review B*, **2004**, 69,	3.3	38
89	Single carrier localization in InxGa1−xAs1−yNy investigated by magnetophotoluminescence. *Applied Physics Letters*, **2004**, 84, 2295-2297	3.4	10

88	Effect of lattice ionicity on hydrogen activity in II-VI materials containing isoelectronic oxygen impurities. *IEE Proceedings: Optoelectronics*, **2004**, 151, 465-468		1
87	Tuning of the electron effective mass and exciton wavefunction size in GaAs1-xNx. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 21, 747-751	3	1
86	Hydrogenation of strain engineered InAs/InxGa1-x As quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2004**, 1, 581-584		2
85	Role of hydrogen in improving optical quality of GaNAs alloys. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 20, 313-316	3	
84	Direct experimental evidence for unusual effects of hydrogen on the electronic and vibrational properties of GaNxP1-x alloys: A proof for a general property of dilute nitrides. *Physical Review B*, **2004**, 70,	3.3	21
83	Temperature dependence and bowing of the bandgap in ZnSe1-xOx. *Applied Physics Letters*, **2004**, 84, 3304-3306	3.4	30
82	Unusual properties of metastable (Ga,In)(N,As) containing semiconductor structures. *IEE Proceedings: Optoelectronics*, **2003**, 150, 28		7
81	Atomic ordering in (InGa)(AsN) quantum wells: An In K-edge X-ray absorption investigation. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 200, 34-39	1.2	8
80	Hydrogen-related effects in diluted nitrides. *Physica B: Condensed Matter*, **2003**, 340-342, 371-376	2.8	3
79	Hydrogen as a probe of the electronic properties of (InGa)(AsN)/GaAs heterostructures. *Solid-State Electronics*, **2003**, 47, 447-453	1.7	3
78	Exciton dynamics in InGaAsN/GaAs heterostructures. *Physica Status Solidi A*, **2003**, 195, 558-562		
77	Emission energy and polarization tuning of InAs/GaAs self-assembled quantum dots by growth interruption. *Journal of Crystal Growth*, **2003**, 251, 192-195	1.6	8
76	Nitrogen passivation induced by atomic hydrogen: The GaP1-yNy case. *Physical Review B*, **2003**, 67,	3.3	51
75	Lattice relaxation by atomic hydrogen irradiation of III-N-V semiconductor alloys. *Physical Review B* , **2003**, 68,	3.3	36
74	Hydrogen-induced improvements in optical quality of GaNAs alloys. *Applied Physics Letters*, **2003**, 82, 3662-3664	3.4	45
73	Role of the host matrix in the carrier recombination of InGaAsN alloys. *Applied Physics Letters*, **2003**, 82, 2805-2807	3.4	13
72	Magnetophotoluminescence studies of (InGa)(AsN)/GaAs heterostructures. *Physical Review B*, **2003**, 67,	3.3	38
71	Photoreflectance evidence of the N-induced increase of the exciton binding energy in an InxGa1-xAs1-yNy alloy. *Applied Physics Letters*, **2003**, 83, 470-472	3.4	19

70	Early manifestation of localization effects in diluted Ga(AsN). *Applied Physics Letters*, **2003**, 82, 4474-4476	3.4	53
69	Global changes of the band structure and the crystal lattice of Ga(N,As) due to hydrogenation. *Physical Review B*, **2003**, 67,	3.3	39
68	Photoluminescence and Infrared Absorption Study of Isoelectronic Impurity Passivation by Hydrogen. *Materials Research Society Symposia Proceedings*, **2002**, 719, 941		
67	Nitrogen-Related Complexes in Ga(AsN) and Their Interaction with Hydrogen. *Physica Status Solidi A*, **2002**, 190, 651-654		
66	Linewidth broadening of excitonic luminescence from quantum wells in pulsed magnetic fields. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 349-352	3	3
65	Reversibility of the effects of hydrogen on the electronic properties of InxGa1−xAs1−yNy. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 1082-1085	3	
64	Electrical and optical properties of self-assembled quantum dots. *Microelectronics Journal*, **2002**, 33, 313-318	1.8	3
63	Photoreflectance investigation of hydrogenated (InGa)(AsN)/GaAs heterostructures. *European Physical Journal B*, **2002**, 30, 39-43	1.2	9
62	Reduced temperature dependence of the band gap in GaAs1−yNy investigated with photoluminescence. *Physical Review B*, **2002**, 65,	3.3	22
61	Role of N clusters in InxGa1−xAs1−yNy band-gap reduction. *Physical Review B*, **2002**, 66,	3.3	18
60	Hydrogen-induced passivation of nitrogen in GaAs1−yNy. *Physical Review B*, **2002**, 65,	3.3	22
59	Structure and passivation effects of mono- and dihydrogen complexes in GaAsyN(1-y) alloys. *Physical Review Letters*, **2002**, 89, 216401	7.4	50
58	Role of hydrogen in III−N−V compound semiconductors. *Semiconductor Science and Technology*, **2002**, 17, 797-802	1.8	27
57	Photoreflectance study of hydrogenated (InGa)(AsN)/GaAs heterostructures. *Materials Research Society Symposia Proceedings*, **2002**, 744, 1		
56	Interplay of nitrogen and hydrogen in InxGa1−xAs1−yNy/GaAs heterostructures. *Physica B: Condensed Matter*, **2001**, 308-310, 850-853	2.8	4
55	Piezoelectric Effects on the Electron−Hole Dipole in In0.5Ga0.5As/GaAs Self-Assembled Quantum Dots. *Physica Status Solidi (B): Basic Research*, **2001**, 224, 37-40	1.3	4
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